TOSHIBA TRANSISTOR SILICON PNP EPITAXIAL TYPE (PCT PROCESS)

## 2 S A 1 0 4 8

## AUDIO FREQUENCY AMPLIFIER APPLICATIONS

Unit in mm

Small Package

High Voltage :  $V_{CEO} = -50V (Min.)$ 

High hff :  $h_{FE} = 70 \sim 400$ 

Excellent hFE Linearity

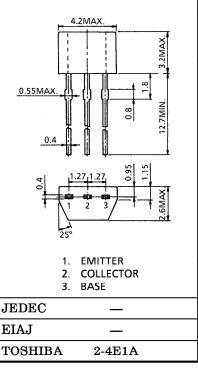
:  $h_{FE} (I_C = -0.1 \text{mA}) / h_{FE} (I_C = -2 \text{mA}) = 0.95 (Typ.)$ 

Low Noise : NF = 1dB (Typ.), 10dB (Max.)

Complementary to 2SC2458

## MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V <sub>CBO</sub>	-50	V
Collector-Emitter Voltage	$v_{CEO}$	-50	V
Emitter-Base Voltage	V <sub>EBO</sub>	-5	V
Collector Current	I <sub>C</sub>	-150	mA
Base Current	$I_{B}$	-50	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	200	mW
Junction Temperature	$T_{j}$	125	°C
Storage Temperature Range	$T_{ m stg}$	-55~125	°C



Weight: 0.13g

## ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I <sub>CBO</sub>	$V_{CB} = -50V, I_E = 0$	_		-0.1	$\mu$ <b>A</b>
Emitter Cut-off Current	${ m I}_{ m EBO}$	$V_{EB} = -5V, I_C = 0$	_		-0.1	$\mu$ <b>A</b>
DC Current Gain	hFE (Note)	$V_{CE} = -6V, I_{C} = -2mA$	70		400	
Collector-Emitter Saturation Voltage	V <sub>CE (sat)</sub>	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$	_	-0.1	-0.3	V
Transition Frequency	$\mathbf{f_T}$	$V_{CE} = -10V, I_{C} = -1mA$	80		_	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB} = -10V, I_E = 0, f = 1MHz$	_	4	7	рF
Noise Figure	NF	$V_{\text{CE}}$ = -6V, $I_{\text{C}}$ = -0.1mA f=1kHz, $R_{\text{G}}$ = 10k $\Omega$	_	1.0	10	dB

 $0:70\sim140,$  $Y: 120 \sim 240$ , GR: 200~400 Note: hFE Classification

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